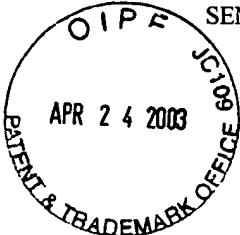


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Election  
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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of: )  
Shunpei YAMAZAKI et al. ) Group Art Unit: 2813  
Serial No. 10/081,767 ) Examiner: Thanh Nguyen  
Filed: February 25, 2002 )  
For: METHOD OF MANUFACTURING A ) Date: April 24, 2003  
SEMICONDUCTOR DEVICE )



RESPONSE TO ELECTION OF SPECIES

Commissioner for Patents  
Washington, D.C. 20231

Sir:

In response to the Request for Restriction mailed March 11, 2003, please amend the above identified application as follows.

IN THE CLAIMS:

Please add new claims 78-81 as follows:

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78. (New) A method of manufacturing a semiconductor device, said method comprising the steps of:

irradiating a semiconductor film with a laser light to improve crystallinity of the semiconductor film wherein a warp is created in the semiconductor film due to the irradiation of the laser light;

heating the crystallized semiconductor film in order to decrease the warp; and

etching the crystallized semiconductor film to form at least one semiconductor

island after said heating

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02 FC:1204 84.00 CH

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